

Abstract

The present invention provides a semiconductor device capable of preventing a pattern collapse phenomenon in a cell edge area in which a pattern is more fragile. The inventive semiconductor device having a lower pattern density in an edge area than in a central area of a wafer includes a plurality of bar-type patterns allocated at a predetermined distance in the central area of the wafer; a plurality of dummy patterns formed in the edge area; and a plurality of a connection pattern for coupling at least two of the bar-type patterns to each other, wherein the connection patterns of the plurality of dummy patterns is allocated in a zigzag fashion.